

UV-A Sensor

GUVV-S10SD



Features

- Indium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- High Responsivity & Low Dark Current



Applications

- Pure UV-A Monitoring
- Counterfeit Money Detection

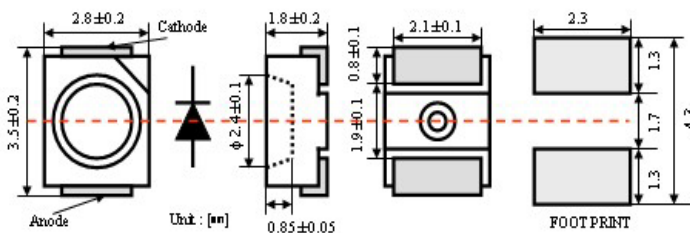
Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90		
Operating Temperature	T_{op}	-30	85		
Reverse Voltage	$V_{r, max.}$		3	V	
Forward Current	$I_{f, max.}$		1	mA	
Soldering Temperature	T_{sol}		260		within 10 sec.

Characteristics (at 25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d		0.05	1	nA	$V_r = 1.0 V$
Photo Current	I_{ph}		65		nA	UVA Lamp, $1mW/cm^2$
Temperature Coefficient	I_{tc}		0.1		%/°C	UVA Lamp
Responsivity	R		0.11		A/W	$\lambda = 350 nm, V_r = 0 V$
Spectral Detection Range	λ	240		395	nm	
Breakdown Voltage	V_{BR}		5		V	$I_r = 1 \mu A$

Outline Diagrams and Dimensions



Responsivity curve

